

Description

The SPF6102 is 3-phase Brushless Motor Driver IC. The IC is suitable for the applications which the maximum applied voltage to the motor is 150 V or less.

The IC is driven by a bootstrap circuit, and the charge to this boost power supply (boot capacitor) is supplied from the internal auxiliary power supply. This auxiliary power supply is boosted by the internal charge pump circuit and supplies a stable voltage that does not depend on the automotive inherent battery variation to the gate drive circuit.

The IC uses the compact SMD package, HSOP48 with high thermal dissipation and provides high-density mounting. Since the IC has the various protection functions, it can drive 3-phase brushless motor with few external components.

Features

- AEC-Q100 Qualified
- Built-in Bootstrap Diode
- Built-in Auxiliary Power Supply (VREGx)
- Bare Lead Frame: Pb-free (RoHS compliant)
- Enable Function (All phases shutdown with EN = logic low)
- Fault Signal Output at Protect Circuit Activated
- Protections
- Simultaneous On-state Prevention
- VBB Pin Overvoltage Protection (VBB_OVP): Autorestart
- Undervoltage Lockout
 VBB Pin (VBB_UVLO): Auto-restart
 VDD Pin (VDD_UVLO): Auto-restart
 VREGx Pin (VREGx_UVLO): Auto-restart
- Thermal Shutdown (TSD)

Typical Application

Package

HSOP48



Not to scale

Specifications

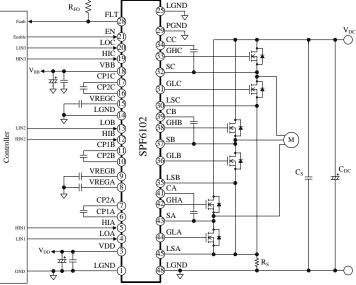
- Maximum Main Supply Voltage: V_{DC} = 150 V
- Maximum Logic Supply Voltage: VBB = 35 V
- Typical On-resistance of Internal Drive Circuit Sink: 4 Ω

Source: 5 Ω

Applications

For driving 3-phase DC brushless motor such as:

- Electronic Power Steering (EPS)
- Integrated Starter Generator (ISG) Hybrid System
- Radiator Pump
- Fan for Air Conditioner



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1. Absolute Maximum Ratings

Current polarities are defined as follows: current going into the IC (sinking) is positive current (+); and current coming out of the IC (sourcing) is negative current (–).

Parameter	Symbol	Conditions	Ratings	Unit
Direct Comment Insert Vielte er	V_{BB1}		-0.6 to 35	V
Direct Current Input Voltage	V _{BB2}	T < 400 ms	40	V
VREGx Pin Voltage	V _{REG}		-0.6 to 18	V
VDD Pin Voltage	V_{DD}		-0.3 to 6	V
HIx, LOx and EN Pin Voltage	V _{IN}		-0.3 to 6	V
LSx Pin Voltage	V _{LSx}		-4 to 4	V
GLx Pin Voltage	V _{GLx}		-4 to 18	V
Sx Pin Voltage	V _{Sx}		-4 to 132	V
GHx Pin Voltage	V_{GHx}		-4 to 150	V
Cx Pin Voltage	V _{Cx}		-0.3 to 150	V
FLT Pin Voltage	V _{FLT}		-0.3 to 6	V
CP1x Pin Voltage	V _{CP1x}		-0.3 to 18	V
CP2x Pin Voltage	V _{CP2x}		-0.3 to 18	V
	P _{D1}	Infinite Heatsink	30.4	W
Power Dissipation	P _{D2}	Glass-epoxy Board*	3.57	W
Junction Temperature	T_{J}		-40 to 150	°C
Operating Ambient Temperature	T _{OP}		-40 to 105	°C
Storage Temperature	T _{STG}		-40 to 150	°C
Junction-to-Case Thermal Resistance	$\theta_{J\text{-}C}$		4.1	°C/W
Junction-to-Ambient Thermal Resistance	$\theta_{J\text{-}A}$		35	°C/W

Unless specifically noted, $T_A = 25$ °C, and reference ground is the LGND pin.

* Board size is 50 mm \times 74 mm, thickness of glass-epoxy is 1.6 mm, and thickness of copper laminate is 18 μ m.

2. Recommended Operating Conditions

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
VBB Pin Input Supply Voltage	V_{BB}		7	14	18	V
VDD Pin Input Supply Voltage	V _{DD}		4.5	5.0	5.5	V

3. **Electrical Characteristics**

Current polarities are defined as follows: current going into the IC (sinking) is positive current (+); and current coming out of the IC (sourcing) is negative current (–). Unless specifically noted, $T_A = -30$ °C to 125 °C, $V_{BB} = 14$ V, $V_{DD} = EN = 5$ V, $C_{REGx} = 10 \ \mu\text{F}$, $f_{PWM} = 22.5 \text{ kHz}$,

and $C_{Px} = C_{Bx} = 0.1 \ \mu F$.

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
VBB Input Current 1	I_{BB1}	VDD = EN = 0 V $HIx = LOx = 5 V$		5		mA
VBB Input Current 2				15		mA
VDD Input Current	I _{DD}	HIx = LOx = 5 V		1.0	5.0	mA
Cx Pin, GHx Pin, Sx Pin Current	I _{CxL}	Cx = GHx = Sx = 90 V		_	100	μA
VREGx Output Voltage 1	V _{REGx1}	7 V < VBB < 8 V	10	12	15	V
VREGx Output Voltage 2	V _{REGx2}	$8 \text{ V} \leq \text{VBB}$	12	15	18	V
Enable Voltage	V _{ENH}		2.0	_		V
Enable Release Voltage	V _{ENL}	HIx = 5 V, LSx = Sx = LGND			0.8	V
Enable Voltage Hysteresis	ΔV_{EN}	L5x - 5x - L010		0.15		V
HIx Pin Logic Low Input Voltage	V _{HIxH}				0.8	v
HIx Pin Logic High Input Voltage	V _{HIxL}	HIx = 5 V, LSx = Sx = LGND	2.0			v
HIx Pin Input Voltage Hysteresis	ΔV_{HIx}	L3x - 3x - L010		0.15		v
LOx Pin Logic Low Input Voltage	V _{LOxH}				0.8	v
LOx Pin Logic High Input Voltage	V _{LOxL}	LOx = 5 V, LSx = Sx = LGND	2.0			v
LOx Pin Input Voltage Hysteresis	ΔV_{LOx}	L3x - 3x - L0MD		0.15		V
EN Pin Input Current (H)	I _{ENH}	EN = 5 V		100	500	μA
EN Pin Input Current (L)	I _{ENL}	EN = 0 V	-100			μA
HIx Pin Input Current (H)	I _{HIxH}	HIx = 0 V	-500	-100		μA
HIx Pin Input Current (L)	I _{HIxL}	HIx = 5 V		_	100	μA
LOx Pin Input Current (H)	I _{LOxH}	LOx = 0 V	-500	-100		μA
LOx Pin Input Current (L)	I _{LOxL}	LOx = 5 V			100	μA
FLT Pin Output Saturation Voltage	V _{FLT}	$I_{FLT(L)} = 1 \text{ mA}$	_		0.4	v
Bootstrap Diode Forward Voltage	V _{TH(BD)}	$I_F = 1 \text{ mA}$	0.4	1.2	1.7	v
GHx Pin Source On-resistance	R _{DS(SC_GHx)}	HIx = 0 V,	3	5.0	10	Ω
GHx Pin Sink On-resistance	$\begin{array}{c} \text{LOx} = 5 \text{ V},\\ \text{LOx} = 5 \text{ V},\\ \text{LSx} = \text{Sx} = \text{LGND},\\ \text{Cx} > 10 \text{ V},\\ \text{VREGx} > 10 \text{ V} \end{array}$		2	4.0	8	Ω
GLx Pin Source On-resistance	R _{DS(SC_GLx)}	HIx = 5 V,	3	5.0	10	Ω
Contract		LSx = Sx = LGND, Cx > 10 V,	2	4.0	8	Ω
High side Output Dalar Time	t _{on(H)x}	Ciss = 3300 pF,		250		ns
High-side Output Delay Time	t _{off(H)x}	see Figure 3-1		200		ns
Low side Output Delay Time	t _{on(L)x}	Ciss = 3300 pF,		250		ns
Low-side Output Delay Time	t _{off(L)x}	see Figure 3-1		200		ns

SPF6102

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
GHx Pin Output Rise Time ⁽¹⁾	t _{r(GHx)}	$20\% V_{GHx}$ to $80\% V_{GHx}$,	10		100	ns
GHx Pin Output Fall Time ⁽¹⁾	t _{f(GHx)}	Ciss = 3300 pF, see Figure 3-1	10	_	100	ns
GLx Pin Output Rise Time ⁽¹⁾	t _{r(GLx)}	$20\% V_{GLx}$ to $80\% V_{GLx}$,	10	_	100	ns
GLx Pin Output Fall Time ⁽¹⁾	t _{f(GLx)}	Ciss = 3300 pF, see Figure 3-1	10		100	ns
VDD Pin Undervoltage Lockout Release Voltage	V _{UVDD(H)}			4.0		v
VDD Pin Undervoltage Lockout Operating Voltage	V _{UVDD(L)}			3.8	_	V
VDD Pin Undervoltage Lockout Hysteresis	$\Delta V_{\rm UVDD}$			0.2	_	v
VBB Pin Overvoltage Protection Operating Voltage	$V_{OVBB(H)}$		_	28	_	v
VBB Pin Overvoltage Protection Release Voltage	V _{OVBB(L)}			25	_	V
VBB Pin Overvoltage Protection Hysteresis	ΔV_{OVBB}			3	_	V
VBB Pin Undervoltage Lockout Release Voltage	$V_{UVBB(H)}$		6.0	6.5	7.0	V
VBB Pin Undervoltage Lockout Operating Voltage	$V_{UVBB(L)}$		5.5	6.1	6.6	V
VBB Pin Undervoltage Lockout Hysteresis	$\Delta V_{\rm UVBB}$			0.4	—	V
VREGx Pin Undervoltage Lockout Release Voltage	V _{UVREGx(H)}		6.5	7.5	8.5	v
VREGx Pin Undervoltage Lockout Operating Voltage	V _{UVREGx(L)}		6.0	7.1	8.2	v
VREGx Pin Undervoltage Lockout Hysteresis	ΔV_{UVREGx}		_	0.4		v
Thermal Shutdown Starting Temperature ⁽²⁾	T _{TSD}		151			°C

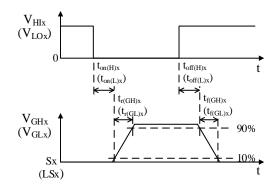


Figure 3-1. Definition of Switching Time

• Turning on: $I_{SOURCE} = 2.0 \text{ A}$

• Turning off: $I_{SINK} = 2.3 A$

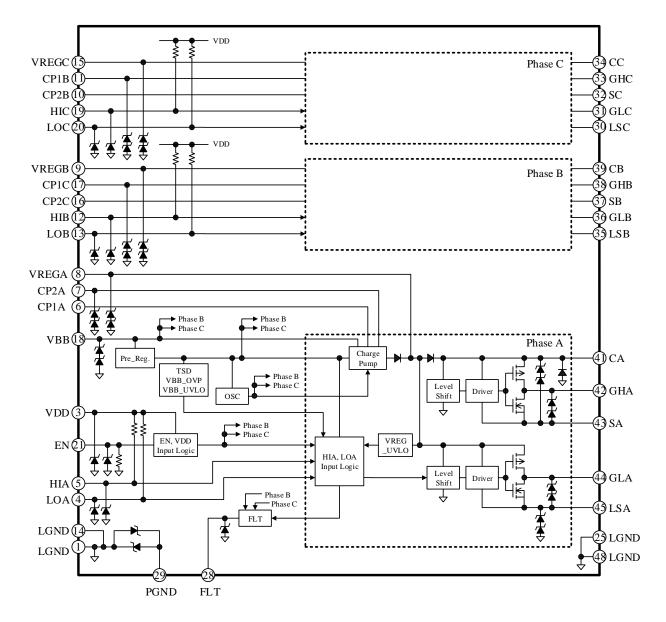
 $^{(2)}$ It is guaranteed by design. The typical design value of thermal shutdown starting temperature is 165 °C.

⁽¹⁾ When the outputs of the GHx and GLx pins are turned on/ off, the typical design values of output pulse current of the GHx and GLx pins are as follows (conditions: VREGx = 15 V, t < 100 ns, and $T_A = 25$ °C):

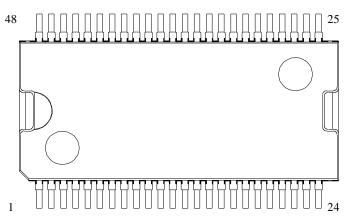
4. Mechanical Characteristics

Parameter	Min.	Тур.	Max.	Unit
Package Weight		0.99		g

5. Block Diagram



6. Pin Configuration Definitions



1 LGND Control ground 25 LGND Control ground 2 (NC) (No connection) 26 (NC) (No connection) 3 VDD Logic supply input for input signal 27 (NC) (No connection) 4 LOA Low-side logic input for A-phase 28 FLT Fault signal output (Open drain) 5 HIA High-side logic input for A-phase 29 PGND Power ground 6 CP1A Capacitor connect pin 1 for A-phase 30 LSC C-phase low-side gate drive signal output (New signal output in the sis a signal output in the sis a signal output in the s	Pin Number	Pin Name	Function	Pin Number	Pin Name	Function
3 VDD Logic supply input for input signal 27 (NC) (No connection) 4 LOA Low-side logic input for A-phase 28 FLT Fault signal output (Open drain) 5 HIA High-side logic input for A-phase 29 PGND Power ground 6 CP1A Capacitor connect pin 1 for A-phase 30 LSC C-phase low-side gate drive signal output 7 CP2A Capacitor connect pin 1 for A-phase inspination output 31 GLC C-phase high-side source connection 9 VREGA Capacitor connect pin 67 A-phase high-and low-side gate drive 32 SC C-phase high-side source connection 9 VREGB Capacitor connect pin 2 for B-phase high-and low-side gate drive gate drive 33 GHC C-phase high-side gate drive signal output 10 CP2B Capacitor connect pin 2 for B-phase 34 CC C-phase boot capacitor connection 11 CP1B Capacitor connect pin 1 for B-phase 35 LSB B-phase low-side source connection 12 HIB High-side logic input for B-phase 37 SB B-phase high-side source connection 13 LOB </td <td>1</td> <td></td> <td>Control ground</td> <td>1</td> <td></td> <td>Control ground</td>	1		Control ground	1		Control ground
4 LOA Low-side logic input for A-phase 28 FLT Fault signal output (Open drain) 5 HIA High-side logic input for A-phase 29 PGND Power ground 6 CP1A Capacitor connect pin 1 for A-phase charge pump circuit 30 LSC C-phase low-side gate drive signal output 7 CP2A Capacitor connect pin 2 for A-phase charge pump circuit 31 GLC C-phase low-side gate drive signal output 8 VREGA Capacitor connect pin for A-phase high- and low-side gate drive 32 SC C-phase high-side source connection 9 VREGB Capacitor connect pin 2 for B-phase high- and low-side gate drive 33 GHC C-phase boot capacitor connection 10 CP2B Capacitor connect pin 1 for B-phase 34 CC C-phase low-side gate drive signal output 11 CP1B Capacitor connect pin 1 for B-phase 35 LSB B-phase low-side gate drive signal output 12 HIB High-side logic input for B-phase 37 SB B-phase high-side source connection 14 LGND Control ground 38 GHB B-phase bigh-side gate drive signal output	2	(NC)	(No connection)	26	(NC)	(No connection)
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8VREORand low-side gate drive32SCC-phase high-side source connection9VREGBCapacitor connect pin for B-phase high- and low-side gate drive33GHCC-phase high-side gate drive signal output10CP2BCapacitor connect pin 1 for B-phase charge pump circuit34CCC-phase boot capacitor connection11CP1BCapacitor connect pin 1 for B-phase charge pump circuit35LSBB-phase low-side source connection12HIBHigh-side logic input for B-phase36GLBB-phase low-side gate drive signal output13LOBLow side logic input for B-phase37SBB-phase high-side source connection14LGNDControl ground38GHBB-phase high-side gate drive signal output15VREGCCapacitor connect pin 2 for C-phase charge pump circuit39CBB-phase boot capacitor connection16CP2CCapacitor connect pin 1 for C-phase charge pump circuit40(NC)(No connection)17CP1CCapacitor connect pin 1 for C-phase charge pump circuit41CAA-phase bigh-side gate drive signal output19HICHigh side logic input for C-phase43SAA-phase high-side gate drive signal output20LOCLow side Logic input for C-phase43SAA-phase high-side source connection21ENEnable signal input42GHAA-phase high-side source connection22(NC)(No connection) <td< td=""><td>7</td><td>CP2A</td><td>charge pump circuit</td><td>31</td><td>GLC</td><td></td></td<>	7	CP2A	charge pump circuit	31	GLC	
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12HBHigh-side logic input for B-phase36GLBoutput13LOBLow side logic input for B-phase37SBB-phase high-side source connection14LGNDControl ground38GHBB-phase high-side gate drive signal output15VREGCCapacitor connect pin for C-phase high- and low-side gate drive39CBB-phase boot capacitor connection16CP2CCapacitor connect pin 2 for C-phase charge pump circuit40(NC)(No connection)17CP1CCapacitor connect pin 1 for C-phase charge pump circuit41CAA-phase boot capacitor connection18VBBMain supply input42GHAA-phase high-side gate drive signal output19HICHigh side logic input for C-phase charge pump circuit43SAA-phase high-side source connection20LOCLow side Logic input for C-phase charge low-side logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	11	CP1B		35	LSB	B-phase low-side source connection
14LGNDControl ground38GHBB-phase high-side gate drive signal output15VREGCCapacitor connect pin for C-phase high- and low-side gate drive39CBB-phase boot capacitor connection16CP2CCapacitor connect pin 2 for C-phase charge pump circuit40(NC)(No connection)17CP1CCapacitor connect pin 1 for C-phase charge pump circuit41CAA-phase boot capacitor connection18VBBMain supply input42GHAA-phase high-side gate drive signal output19HICHigh side logic input for C-phase charge logic input for C-phase43SAA-phase high-side source connection20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	12	HIB	High-side logic input for B-phase	36	GLB	
14LGNDControl ground38GHBoutput15VREGCCapacitor connect pin for C-phase high- and low-side gate drive39CBB-phase boot capacitor connection16CP2CCapacitor connect pin 2 for C-phase charge pump circuit40(NC)(No connection)17CP1CCapacitor connect pin 1 for C-phase charge pump circuit41CAA-phase boot capacitor connection18VBBMain supply input42GHAA-phase high-side gate drive signal output19HICHigh side logic input for C-phase43SAA-phase high-side source connection20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	13	LOB	Low side logic input for B-phase	37	SB	
15VRECand low-side gate drive39CBB-phase boot capacitor connection16CP2CCapacitor connect pin 2 for C-phase charge pump circuit40(NC)(No connection)17CP1CCapacitor connect pin 1 for C-phase charge pump circuit41CAA-phase boot capacitor connection18VBBMain supply input42GHAA-phase high-side gate drive signal output19HICHigh side logic input for C-phase43SAA-phase high-side source connection20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	14	LGND	-	38	GHB	
16CP2Ccharge pump circuit40(NC)(No connection)17CP1CCapacitor connect pin 1 for C-phase charge pump circuit41CAA-phase boot capacitor connection18VBBMain supply input42GHAA-phase high-side gate drive signal output19HICHigh side logic input for C-phase43SAA-phase high-side source connection20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	15	VREGC	and low-side gate drive	39	СВ	B-phase boot capacitor connection
17CPICcharge pump circuit41CAA-phase boot capacitor connection18VBBMain supply input42GHAA-phase high-side gate drive signal output19HICHigh side logic input for C-phase43SAA-phase high-side source connection20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	16	CP2C	charge pump circuit	40	(NC)	(No connection)
18VBBMain supply input42GHAoutput19HICHigh side logic input for C-phase43SAA-phase high-side source connection20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	17	CP1C		41	CA	
20LOCLow side Logic input for C-phase44GLAA-phase low-side gate drive signal output21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	18	VBB	Main supply input	42	GHA	
20EocLow side Logic input for C-phase44OLAoutput21ENEnable signal input45LSAA-phase low-side source connection22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	19	HIC	High side logic input for C-phase	43	SA	
22(NC)(No connection)46(NC)(No connection)23(NC)(No connection)47(NC)(No connection)	20	LOC	Low side Logic input for C-phase	44	GLA	
23 (NC) (No connection) 47 (NC) (No connection)	21	EN	Enable signal input	45	LSA	A-phase low-side source connection
	22	(NC)	(No connection)	46	(NC)	(No connection)
24 (NC) (No connection) 48 LGND Control ground	23	(NC)	(No connection)	47	(NC)	(No connection)
	24	(NC)	(No connection)	48	LGND	Control ground

7. Typical Application

In the case of the application so that the LSx pin voltage exceeds the absolute maximum rating of ± 4 V, a diode, D_s, must be added between the LSx pin and the LGND pin.

If the GLx pin voltage becomes lower by about 0.6 V to 1.8 V than the LSx pin voltage, the IC may be damaged. To avoid the situation, a diode, D_{GX} , must be added between the GLx pin and the LSx pin.

D_S and D_{Gx} must be placed near the IC, and connected with a minimal length of traces.

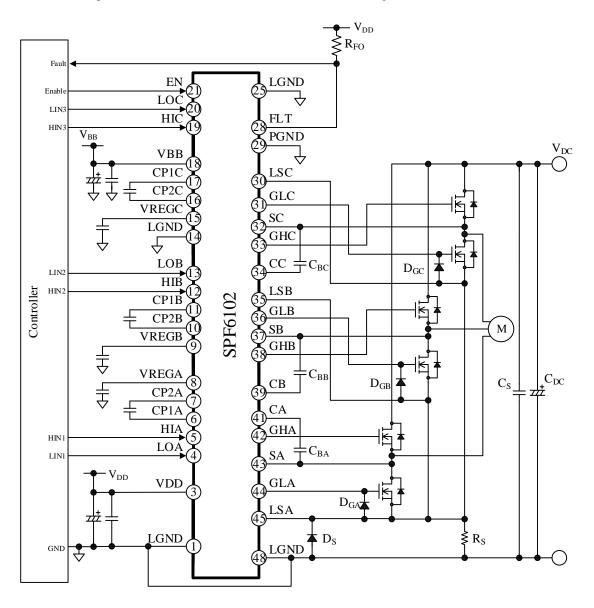


Figure 7-1. Typical Application

8. Truth Table

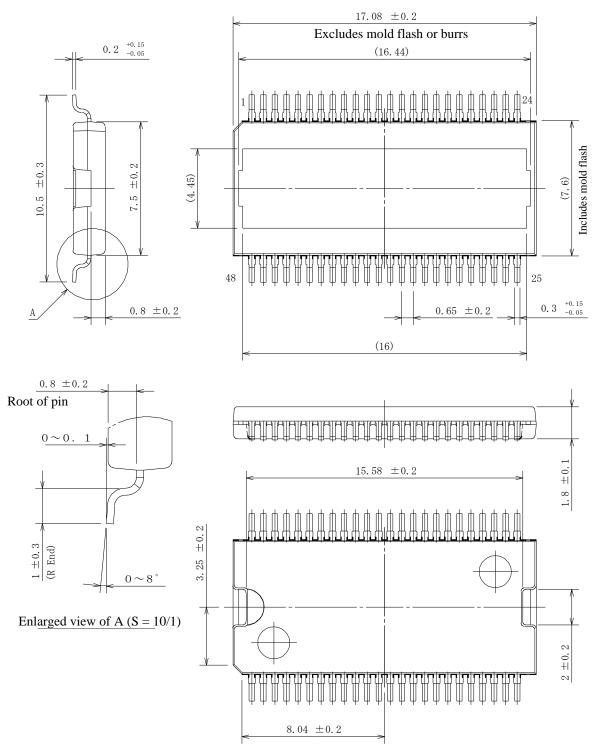
M. L	Inpu	t Pin	Output Pin			Demenia	
Mode	HIx	LOx	GHx	GLx	FLT*	Remarks	
	Н	Н	L	L	Н		
	L	Н	Н	L	Н		
Normal Operation	Н	L	L	Н	Н		
-	L	L	L	L	Н	Simultaneous On-state Prevention	
	Н	Н	L	L	L		
VBB Pin	L	Н	L	L	L		
Undervoltage Lockout (VBB_UVLO)	Н	L	L	L	L		
(()))	L	L	L	L	L		
	Н	Н	L	L	L		
VDD Pin	L	Н	L	L	L		
Undervoltage Lockout (VDD_UVLO)	Н	L	L	L	L		
(100_0100)	L	L	L	L	L		
	Н	Н	L	L	Н		
Enable Signal Input	L	Н	L	L	Н		
(EN pin is low level)	Н	L	L	L	Н		
	L	L	L	L	Н		
	Н	Н	L	L	L		
VREGx Pin	L	Н	Н	L	L		
Undervoltage Lockout	Н	L	L	Н	L		
(VREGx_UVLO)	L	L	L	L	L	Simultaneous On-state Prevention	
	Н	Н	L	L	L		
Thermal Shutdown (TSD)	L	Н	L	L	L		
Thermal Shudowii (TSD)	Н	L	L	L	L		
	L	L	L	L	L		

Table 8-1. Truth Table for Operation Modes

*The FLT pin is pulled up to the VDD pin.

9. Physical Dimensions

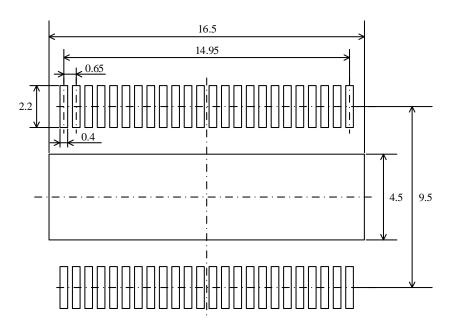
• HSOP48 Package



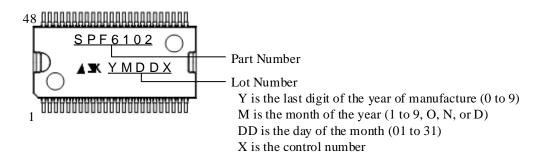
NOTES:

- Dimensions in millimeters
- Bare lead frame: Pb-free (RoHS compliant)

• HSOP48 Land Pattern Example



10. Marking Diagram



11. Operational Descriptions

All the characteristic values given in this section are typical values, unless they are specified as minimum or maximum. Current polarities are defined as follows: current going into the IC (sinking) is positive current (+); and current coming out of the IC (sourcing) is negative current (-).

For pin descriptions, this section employs a notation system that denotes a pin name or an electronic symbol name with the arbitrary letter "x", depending on context. The A, B, and C phases of 3-phase motor are represented as the alphabets A, B, and C, respectively. Thus, "(the) HIx pin" is used when referring to either or all of the HIA, HIB, or HIC pin.

11.1. Pin Descriptions

11.1.1. VBB

This is the main supply input pin of the IC. Recommended applied voltage to the VBB pin is 7 V to 18 V.

When the same power supply is connected to the VBB pin and the external output transistors, power supply loop trace should be designed as wide and short as possible. A Bypass capacitor for noise reduction should be connected to the VBB pin as needed. The bypass capacitor should be placed near the VBB pin, and connected to the VBB pin with a minimal length of traces.

11.1.2. VDD

This is the supply input for input logic circuit. Recommended applied voltage to the VDD pin is 4.5 V to 5.5 V.

11.1.3. VREGx

The power supply of high- and low-side gate drive circuit is generated by the internal charge pump circuit. Thus, the gate can be driven stably even if the VBB pin voltage is low (7 V or more).

Capacitor (10 μ F or more is recommended) for holding supply voltage of gate drive circuit should be connected to the VREGx pin. External power supply connection is unnecessary.

11.1.4. CP1x and CP2x

Connect a capacitor for internal charge pump circuit between the CP1x pin and the CP2x pin. The recommended capacitance is $0.1 \,\mu\text{F}$.

11.1.5. Cx

Connect a high-side boot capacitor, C_{Bx} , between the Cx pin and the Sx pin. The recommended capacitance of C_{Bx} is 0.1 μ F or more. Since the capacitance depends on the drive frequency and control duty, the setting is required according to the application. For proper startup, turn on the low-side output transistors first, and then charge C_{Bx} up to its maximum capacity.

11.1.6. HIx and LOx

These are the signal input pins. The HIx pin acts as high-side controller whereas the LOx pin acts as low-side controller. Since the HIx and LOx pins incorporate a pull-up resistor, the initial state is high (see the block diagram in Section 4).

The width of the input signals to the HIx and LOx pins is required 500 ns or more.

Note that dead time setting for the input signals of the HIx and LOx pins must be done because the IC does not have a dead time generator. Dead time must be set so that the simultaneous on-state does not occur according to the output transistors to be used.

11.1.7. EN

When the high signal is input to the EN pin, all output signals of the GHx and GLx pins become logic low. Since the EN pin incorporates a pull-down resistor, the initial state is low (see the block diagram in Section 4).

11.1.8. FLT

This is the output pin of fault signal. Pull up the FLT pin because the FLT pin is open drain. When the FLT pin is pulled up to the power supply of 5 V, the recommended pull-up resistor is about 20 k Ω . The FLT pin logic level is high in normal operation, and becomes low when one or more the following protections are activated.

- VBB pin Overvoltage Protection (VBB_OVP)
- VBB pin Undervoltage Lockout (VBB_UVLO)
- VDD pin Undervoltage Lockout (VDD_UVLO)
- VREGx pin Undervoltage Lockout (VREGx_UVLO)
- Thermal Shutdown (TSD)

11.1.9. GHx and GLx

These are the gate drive outputs, and are connected to the gate of external output transistors. The GHx pin acts as high-side controller whereas the GLx pin acts as low-side controller. A pull-down resistor of 100 k Ω (typ.) and protection Zener diodes (the Zener diode) of 18 V (typ.) are internally connected between the GHx pin and

the Sx pin, and between the GLx pin and the LSx pin respectively (see Figure 11-1 and Figure 11-2).

When the current from motor flows to the forward direction of this Zener diode, this may be damaged. In the application that the current flows to the forward direction of the Zener diode, an external diode, D_{Gx} , must be added between the GHx pin and the Sx pin, and between the GLx pin and the LSx pin respectively (see Figure 7-1).

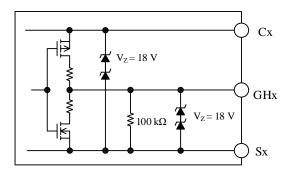


Figure 11-1. Internal Circuit of High-side Output

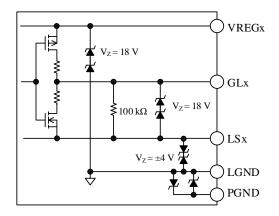


Figure 11-2. Internal Circuit of Low-side Output

11.1.10. Sx and SLx

Connect the Sx pin to the source pin of high-side output transistors and the drain pin of low-side output transistors, and the LSx pin to the source pin of low-side output transistors.

An ESD protection bidirectional Zener diode of ± 4 V is internally connected between the LSx pin and the LGND pin (see Figure 11-2). In the application that the voltage of ± 4 V or more is applied between the Sx pin and the LGND pin, the external diode, D_S, must be connected between the LSx pin and the LGND pin (see Figure 7-1).

11.1.11. LGND and PGND

The LGND pin is control ground of the IC. The PGND pin is power ground. A Zener diode is internally connected bidirectionally between the LGND pin and the PGND pin in parallel (see Figure 11-2).

11.2. Basic Operation

At startup, the voltage is applied to the VBB and VDD pins which are the power supply of the IC. Then, the high signal is input to the EN pin. After that, input the signal to the HIx and LOx pins; and on/off controls of the output transistors start.

When the low signal is input to the HIx pin, high-side gate output (the GHx pin) becomes logic high. When the low signal is input to the LO pin, low-side gate output (the GLx pin) becomes logic high (see Table 8-1).

The EN pin has an internally low-pass filter of $2.5 \ \mu s$ for the noise malfunction prevention. The HIx and LOx pins do not have internal low-pass filter.

11.3. Simultaneous On-state Prevention

When the low signal is input to the HIx and LOx pins at once, the Simultaneous On-state Prevention is activated, and the outputs of the GHx and GLx pins become logic low. This prevents the breakdown of the output transistors.

11.4. Protections

The IC has the following protection functions.

When the following protections are activated, the outputs of the GHx and GLx pins become logic low, and stop the output transistors. In addition, the fault signal is output (the FLT pin logic level becomes low).

When the protection is released after the fault conditions are removed, the FLT output becomes logic high. Then, the GHx and GLx pins restart output the signals according to the input commands on the HIx and LOx pins from the next falling edge.

However, during VREGx_UVLO is activated, the IC outputs the fault signal with maintaining the outputs of the GHx and GLx pins according to input signal.

- VBB Pin Overvoltage Protection (VBB_OVP)
- VBB Pin Undervoltage Lockout (VBB_UVLO)
- VDD Pin Undervoltage Lockout (VDD_UVLO)
- VREGx Pin Undervoltage Lockout (VREGx_UVLO)
- Thermal Shutdown (TSD)

11.4.1. VBB Pin Overvoltage Protection (VBB_OVP)

When the VBB pin voltage increases to the VBB pin overvoltage protection operating voltage $V_{OVBB(H)} = 28$ V or more, VBB_OVP is activated. When the VBB pin voltage decreases to the release voltage $V_{OVBB(L)} = 25$ V or less, the IC returns to the normal operation.

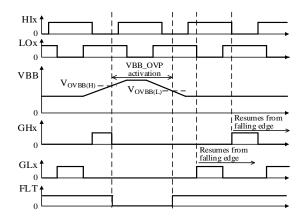


Figure 11-3. Operational Waveform of VBB_OVP

11.4.2. VBB Pin Undervoltage Lockout (VBB_UVLO)

The VBB pin voltage decrease to the VBB pin undervoltage lockout operating voltage $V_{UVBB(L)} = 6.1$ V or less, VBB_UVLO is activated. When the VBB pin voltage increases to the release voltage $V_{UVBB(H)} = 6.5$ V or more, the IC returns to the normal operation. During the VBB_UVLO activation, the internal charge pump circuit (OSC circuit operation is maintained) and the VREG pin boost operation are stopped.

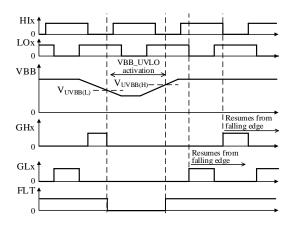


Figure 11-4. Operational Waveform of VBB_UVLO

11.4.3. VDD Pin Undervoltage Lockout (VDD_UVLO)

When the VDD pin voltage decreases to the VDD pin undervoltage lockout operating voltage $V_{UVDD(L)} = 3.8 \text{ V}$ or less, the VDD_UVLO is activated.

When the VDD pin voltage increases to the release voltage $V_{UVDD(H)} = 4.0$ V or more, the IC returns to the normal operation.

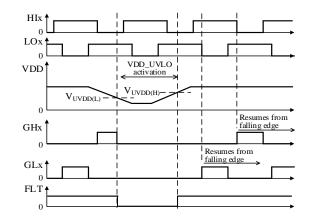


Figure 11-5. Operational Waveform of VDD_UVLO

11.4.4. VREGx Pin Undervoltage Lockout (VREGx_UVLO)

When the VREGx pin voltage decreases to VREGx pin undervoltage lockout operating voltage $V_{UVREGx(L)} = 7.1$ V or less due to the leak current of the capacitor connecting to the VREG pin, the VREGx_UVLO is activated.

When the VREG pin voltage increases to the release voltage $V_{UVREGx(H)} = 7.5$ V or more, the IC returns to the normal operation.

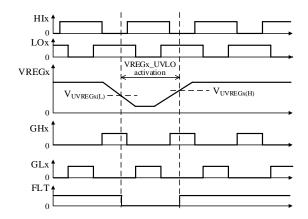


Figure 11-6. Operational Waveform of VREGx_UVLO

11.4.5. Thermal Shutdown (TSD)

When the junction temperature of the IC increases to $T_{TSD} = 151$ °C (min.) or more, the TSD is activated. The design value of TSD operating temperature is 165 °C (typ.). TSD has the temperature hysteresis. When the temperature decreases by about 10 °C from the junction temperature of TSD operation, TSD is released, and the IC returns to the normal operation.

TSD protects the IC against instantaneous heat generation, and does not guarantee the operation including reliability for a state that the heat generation continues for a long time.

11.5. Enable Function

The IC has an enable function.

When the low signal (0.8 V or less) is input to the EN pin, the input signals of the GHx and GLx pins become logic low. When the high signal (2.0 V or more) is input to the EN pin, the GHx and GLx pins restart output the signals according to the input commands on the HIx and LOx pins from the next falling edge. During the EN pin logic is low, the FLT pin logic level is maintained high.

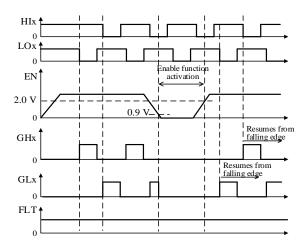


Figure 11-7 Operational Waveform of Enable Function

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